

Silicon Carbide (SiC) Schottky Diode - EliteSiC, 8 A, 1200 V, D1, DPAK

FFSD08120A

Description

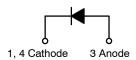
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

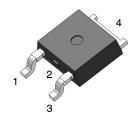
- Max Junction Temperature 175°C
- Avalanche Rated 80 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- This Device is Pb–Free, Halogen Free/BFR Free and RoHS Compliant

Applications

- · General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

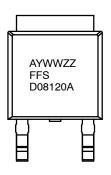


Schottky Diode



DPAK CASE 369AS

MARKING DIAGRAM



A YWW ZZ = Assembly Plant Code= Date Code (Year & Week)

= Lot Code

FFSD08120A = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FFSD08120A

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V_{RRM}	Peak Repetitive Reverse Voltage	1200	V	
E _{AS}	Single Pulse Avalanche Energy (Note 1)	80	mJ	
lF	Continuous Rectified Forward Current @ T _C < 168°C		8	А
	Continuous Rectified Forward Current @ T _C < 135°C		22.5	А
I _{F,Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	530	А
		T _C = 150°C, 10 μs	480	А
I _{F,SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	77	Α
I _{F,RM}	Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	45	Α
P _{TOT}	Power Dissipation	T _C = 25°C	263	W
		T _C = 150°C	44	W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max	0.57	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V _F	Forward Voltage	I _F = 8 A, T _C = 25°C	-	1.45	1.75	V
		I _F = 8 A, T _C = 125°C	_	1.7	2.0	
		I _F = 8 A, T _C = 175°C	_	2.0	2.4	
I _R	Reverse Current	V _R = 1200 V, T _C = 25°C	-	-	200	μΑ
		V _R = 1200 V, T _C = 125°C	-	-	300	
		V _R = 1200 V, T _C = 175°C	-	-	400	
Q_{C}	Total Capacitive Charge	V = 800 V	-	55	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	538	-	pF
		V _R = 400 V, f = 100 kHz	-	50	-	
		V _R = 800 V, f = 100 kHz	_	40	_	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSD08120A	FFSD08120A	DPAK	Tape & Reel [†]	13″	12 mm	2500 Units

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

^{1.} E_{AS} of 80 mJ is based on starting $T_J = 25^{\circ}C$, L = 0.5 mH, $I_{AS} = 18$ A, V = 50 V.

FFSD08120A

TYPICAL CHARACTERISTICS

(T_J = 25°C UNLESS OTHERWISE NOTED)

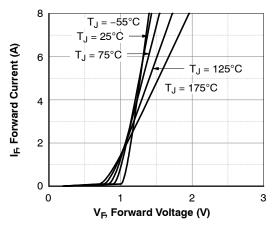


Figure 1. Forward Characteristics

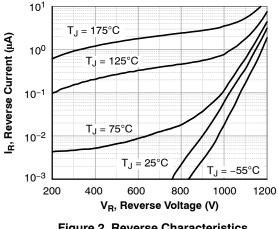


Figure 2. Reverse Characteristics

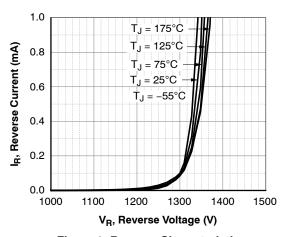


Figure 3. Reverse Characteristics

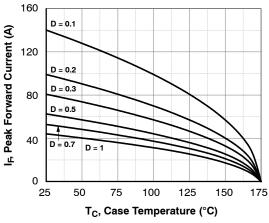


Figure 4. Current Derating

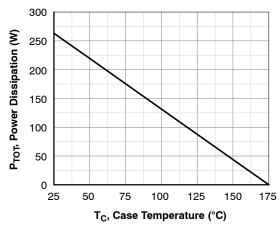


Figure 5. Power Derating

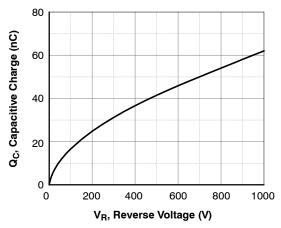


Figure 6. Capacitive Charge vs. Reverse Voltage

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TYPICAL CHARACTERISTICS (CONTINUED)

(T_J = 25°C UNLESS OTHERWISE NOTED)

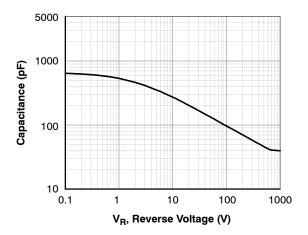


Figure 7. Capacitance vs. Reverse Voltage

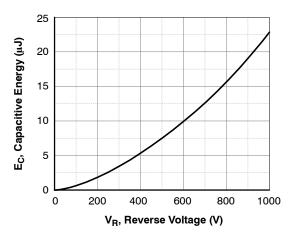


Figure 8. Capacitance Stored Energy

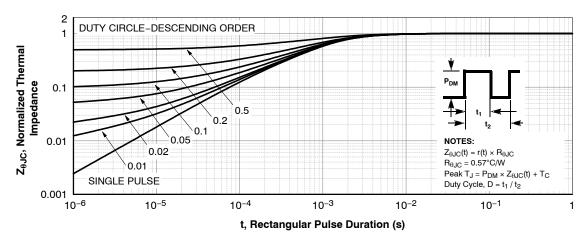
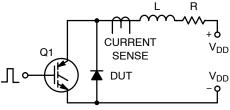


Figure 9. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

 $R < 0.1 \ \Omega$ $V_{DD} = 50 \ V$ $EAVL = 1/2LI2 \left[V_{R(AVL)} / \left(V_{R(AVL)} - V_{DD} \right) \right]$ $Q1 = IGBT \left(BV_{CES} > DUT \ V_{R(AVL)} \right)$

L = 0.5 mH



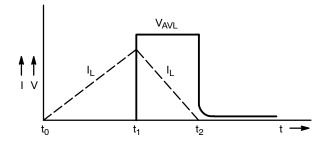
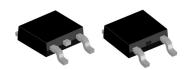


Figure 10. Unclamped Inductive Switching Test Circuit & Waveform





DPAK3 6.10x6.54x2.29, 4.57P CASE 369AS **ISSUE B**

DATE 20 DEC 2023



- NOTES: UNLESS OTHERWISE SPECIFIED

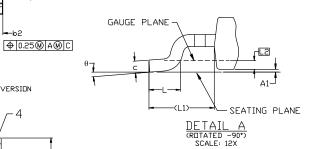
 A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE F, VARIATION AA.

 B) ALL DIMENSIONS ARE IN MILLIMETERS.

 C) DIMENSIONING AND TOLERANCING PER

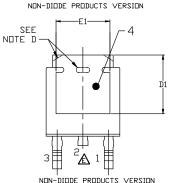
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 - F)

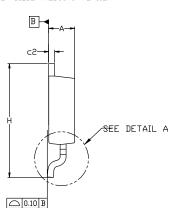
 - DIMENSIONING AND TOLERANCING PER
 ASME Y14.5M-2018.
 SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED
 CORNERS OR EDGE PROTRUSION.
 FOR DIGDE PRODUCTS, L4 IS 0.25 MM MAX PLASTIC BODY
 STUB WITHOUT CENTER LEAD.
 DIMENSIONS ARE EXCLUSIVE OF BURRS,
 MOLD FLASH AND TIE BAR EXTRUSIONS.
 LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD
 T0228P991X239-3N.



MIN. N□M. MAX A 2.18 2.29 2.3 A1 0.00 - 0.16 b 0.64 0.77 0.89	9		
A1 0.00 - 0.12	-		
	7		
la 064 077 009	- /		
N	9		
b2 0.76 0.95 1.14			
b3 5.21 5.34 5.4	6		
c 0.45 0.53 0.63	ı		
c2 0.45 0.52 0.5t	3		
D 5.97 6.10 6.2	2		
D1 5.21	-		
E 6.35 6.54 6.7	3		
E1 4.32	-		
e 2.286 BSC			
e1 4.572 BSC			
H 9.40 9.91 10.4	1		
L 1.40 1.59 1.78	3		
L1 2.90 REF	2.90 REF		
L2 0.51 BSC	0.51 BSC		
L3 0.89 1.08 1.27	7		
L4 1.0a	2]		
θ 0° 10°			

MILLIMETERS





-5.55	MIN-
6.40	6.50 MIN
	2.85 MIN
4.5	1.25 MIN 2.286

LAND PATTERN RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON DUR
PB-FREE STRATEGY AND SOLDERING DETAILS,
PLEASE DOWNLOAD THE ON SEMICONDUCTOR
SOLDERING AND MOUNTING TECHNIQUES
REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*

XXXXXX XXXXXX **AYWWZZ**

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

XXXX = Specific Device Code

= Assembly Location Α

Υ = Year

WW = Work Week

77 = Assembly Lot Code

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